

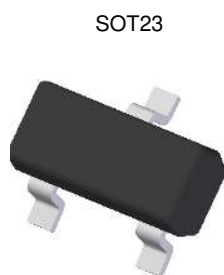
## Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type: MMBT4403
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The MMBT4401Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

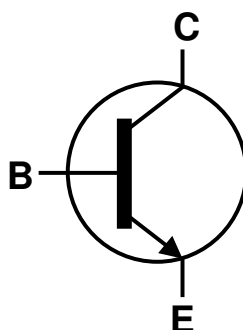
<https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

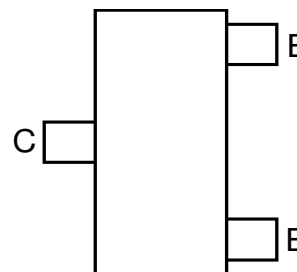
- Package: SOT23
- Package material: molded Plastic "Green" Compound  
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)



Top View



Device Symbol



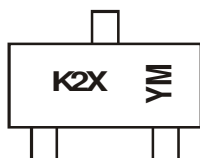
Top View  
Pin-Out

## Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT4401Q-13-F	Automotive	K2X	13	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



K2X = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: I = 2021)  
 M or  $\bar{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2010	.....	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	X	.....	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Absolute Maximum Ratings** (@  $T_A = +25^\circ\text{C}$  unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	600	mA
Peak Collector Current	$I_{CM}$	1	A
Peak Base Current	$I_{BM}$	200	mA

**Thermal Characteristics** (@  $T_A = +25^\circ\text{C}$  unless otherwise specified)

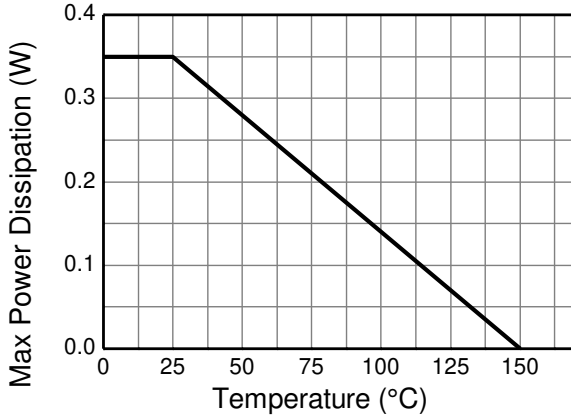
Characteristic	Symbol	Value	Unit
Power Dissipation	$P_D$	(Note 5) 310	mW
		(Note 6) 350	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	(Note 5) 403	$^\circ\text{C/W}$
		(Note 6) 357	
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	350	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	120	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**ESD Ratings** (Note 8)

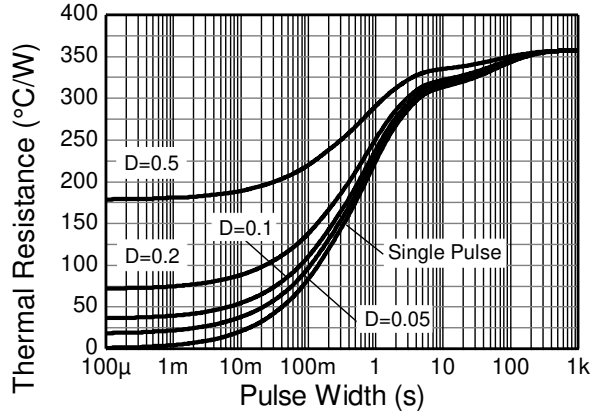
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  6. Same as note (5), except the device is mounted on 15 mm x 15mm 1oz copper.
  7. Thermal resistance from junction to solder-point (at the end of the leads).
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

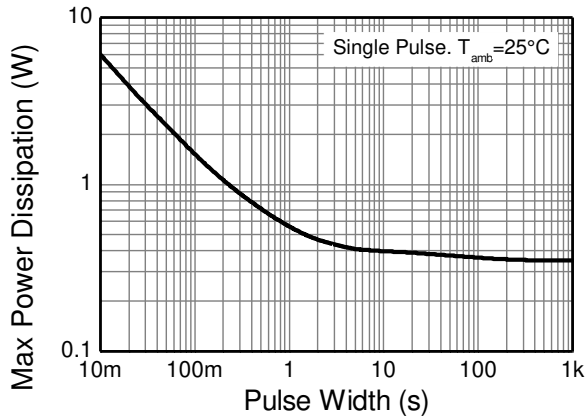
**Thermal Characteristics and Derating Information**



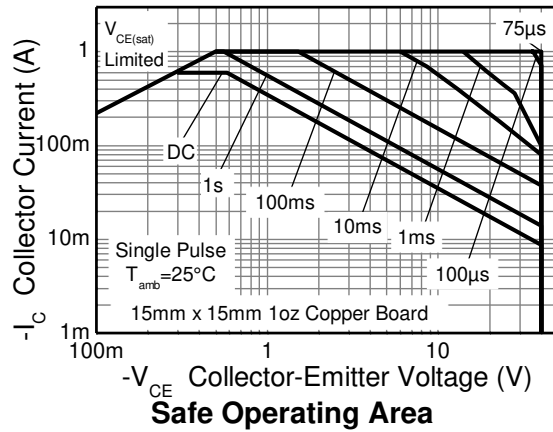
**Derating Curve**



**Transient Thermal Impedance**



**Pulse Power Dissipation**



**Safe Operating Area**

**Electrical Characteristics** (@ T<sub>A</sub> = +25°C unless otherwise specified)

Characteristic	Symbol	Min	Max	Unit	Test Condition	
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	—	V	I <sub>C</sub> = 100μA, I <sub>E</sub> = 0	
Collector-Emitter Breakdown Voltage(Note 9)	BV <sub>CEO</sub>	40	—	V	I <sub>C</sub> = 10.0mA, I <sub>B</sub> = 0	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	—	V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0	
Collector Cutoff Current	I <sub>CEX</sub>	—	100	nA	V <sub>CE</sub> = 35V, V <sub>EB(off)</sub> = 0.4V	
Base Cutoff Current	I <sub>BL</sub>	—	100	nA	V <sub>CE</sub> = 35V, V <sub>EB(off)</sub> = 0.4V	
<b>ON CHARACTERISTICS (Note 9)</b>						
DC Current Gain	h <sub>FE</sub>	20	—	—	I <sub>C</sub> = 100μA, V <sub>CE</sub> = 1.0V	
		40	—			I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 1.0V
		80	—			I <sub>C</sub> = 10mA, V <sub>CE</sub> = 1.0V
		100	300			I <sub>C</sub> = 150mA, V <sub>CE</sub> = 1.0V
		40	—			I <sub>C</sub> = 500mA, V <sub>CE</sub> = 2.0V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	0.40 0.75	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.75 —	0.95 1.2	V	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA	
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Output Capacitance	C <sub>cb</sub>	—	6.5	pF	V <sub>CB</sub> = 5.0V, f = 1.0MHz, I <sub>E</sub> = 0	
Input Capacitance	C <sub>eb</sub>	—	30	pF	V <sub>EB</sub> = 0.5V, f = 1.0MHz, I <sub>C</sub> = 0	
Input Impedance	h <sub>ie</sub>	1.0	15	kΩ	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz	
Voltage Feedback Ratio	h <sub>re</sub>	0.1	8.0	x 10 <sup>-4</sup>		
Small Signal Current Gain	h <sub>fe</sub>	40	500	—		
Output Admittance	h <sub>oe</sub>	1.0	30	μS		
Current Gain-Bandwidth Product	f <sub>T</sub>	250	—	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 20mA, f = 100MHz	
<b>SWITCHING CHARACTERISTICS</b>						
Delay Time	t <sub>d</sub>	—	15	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA, V <sub>BE(off)</sub> = 2.0V, I <sub>B1</sub> = 15mA	
Rise Time	t <sub>r</sub>	—	20	ns		
Storage Time	t <sub>s</sub>	—	225	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA, I <sub>B1</sub> = -I <sub>B2</sub> = 15mA	
Fall Time	t <sub>f</sub>	—	30	ns		

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

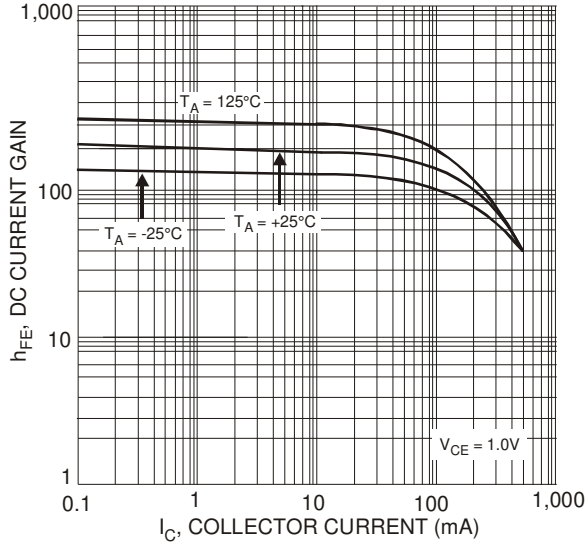


Figure 1 Typical DC Current Gain vs. Collector Current

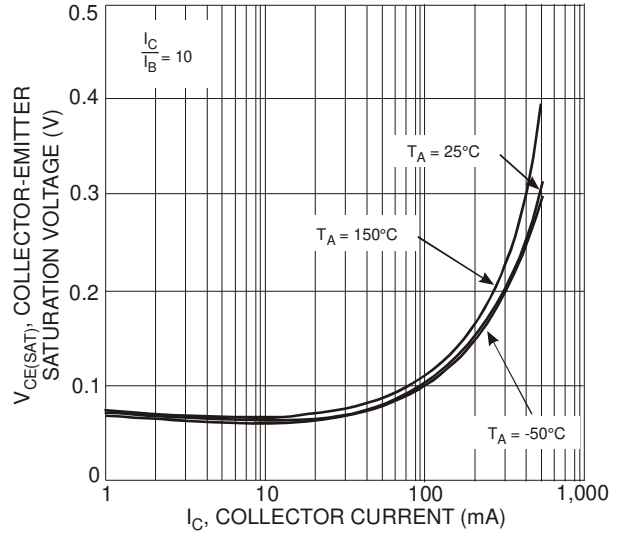


Figure 2 Collector-Emitter Saturation Voltage vs. Collector Current

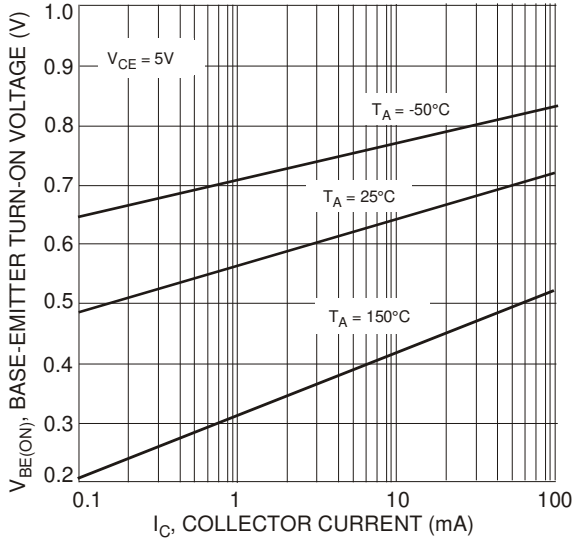


Figure 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

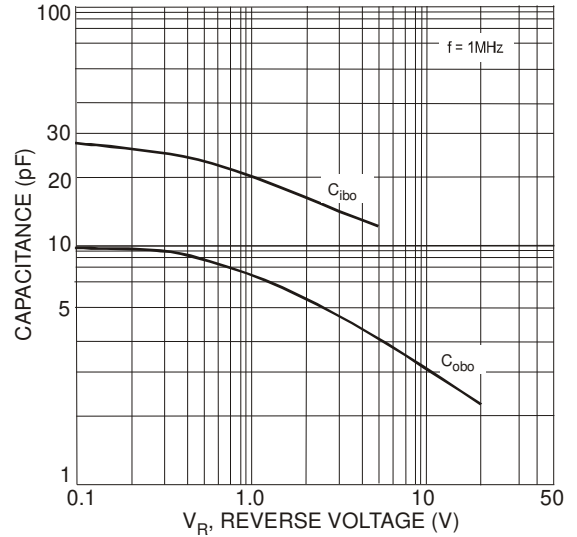


Figure 4 Typical Capacitance Characteristics

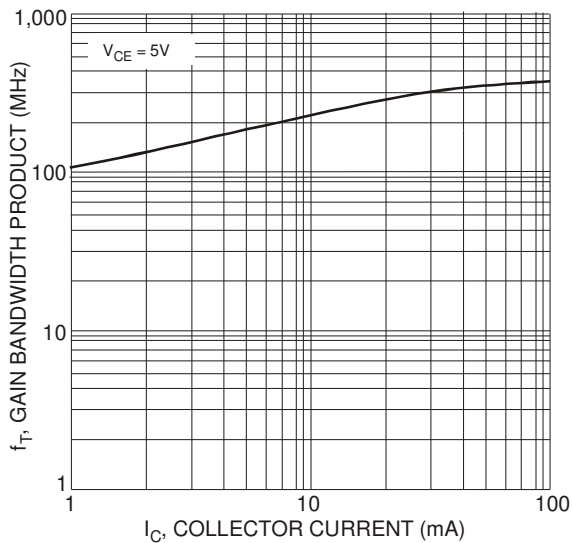


Figure 5 Typical Gain Bandwidth Product vs. Collector Current

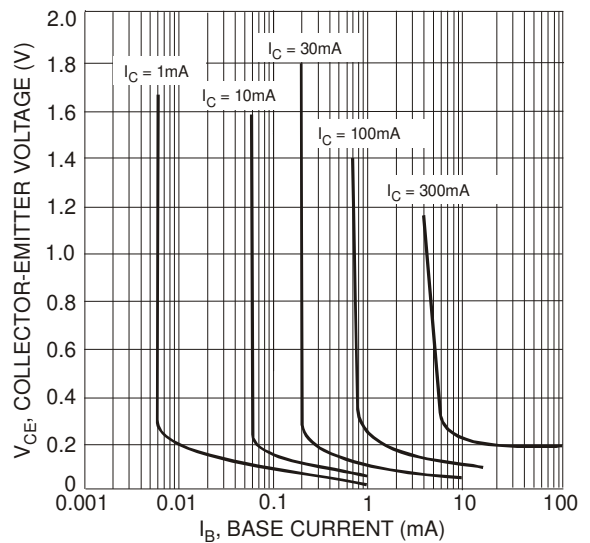
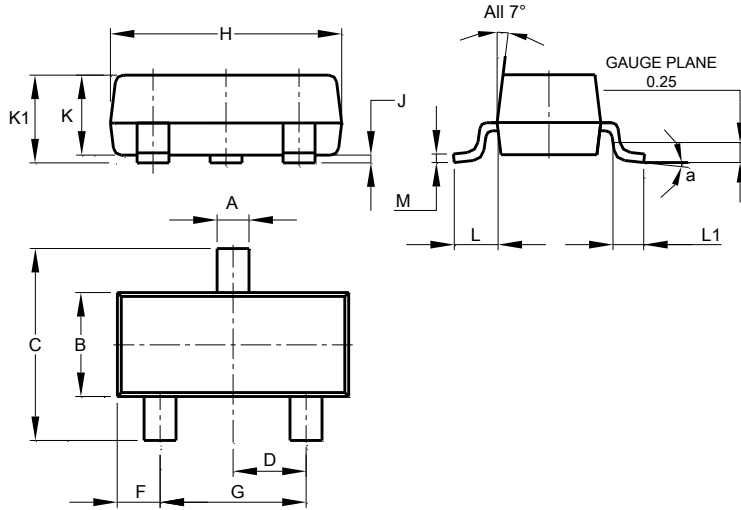


Figure 6 Typical Collector Saturation Region

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**

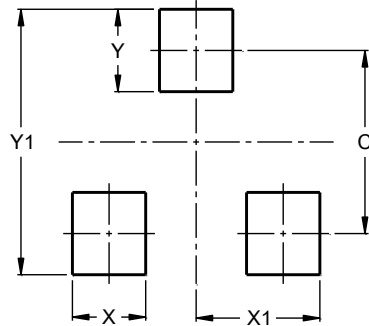


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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